Silicon N-Channel MOS FET

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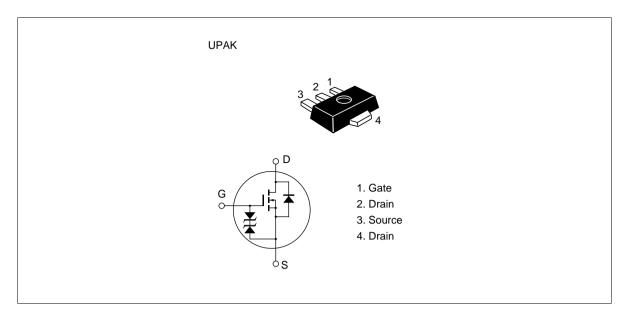
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device - can be driven from 5 V source.
- Suitable for DC DC converter, motor drive, power switch, solenoid drive

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	0.3	А
Drain peak current	l _{D(pulse)} *¹	1.2	A
Body to drain diode reverse drain current	I _{DR}	0.3	A
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

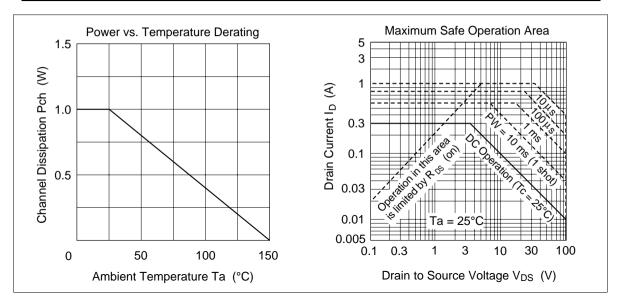
2. When using the alumina ceramic board ($12.5 \times 20 \times 0.7$ mm)

3. Marking is "FY".

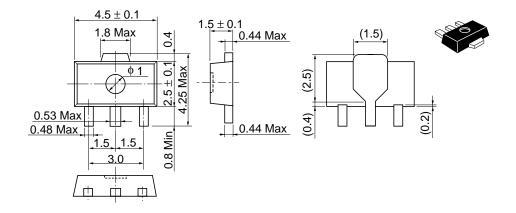
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	100	_	_	V	$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	_	V	$I_{g} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	—	—	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	50	μA	$V_{\rm DS} = 80 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	1.0		2.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	3.5	4.5	Ω	$I_{\rm D} = 0.2$ A, $V_{\rm GS} = 10$ V * ¹
		_	4.5	6.5	Ω	$I_{\rm D}$ = 0.2 A, $V_{\rm GS}$ = 4 V * ¹
Forward transfer admittance	y _{fs}	0.22	0.35	—	S	$I_{\rm D} = 0.2$ A, $V_{\rm DS} = 10$ V *1
Input capacitance	Ciss	_	35		pF	$V_{\rm DS} = 10 \ V, \ V_{\rm GS} = 0,$
Output capacitance	Coss	_	14	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	3.5		pF	
Turn-on delay time	t _{d(on)}	_	2		ns	$I_{\rm D} = 0.2$ A, $V_{\rm GS} = 10$ V,
Rise time	t,	_	4	_	ns	R _L = 150 Ω
Turn-off delay time	t _{d(off)}	_	17	_	ns	
Fall time	t _r	_	15	_	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 0.3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	—	80	—	ns	$I_{F} = 0.3 \text{ A}, V_{GS} = 0,$ $di_{F}/dt = 50 \text{ A}/\mu \text{s}$
Note 1. Pulse test						

See characteristic curve of 2SK1337.



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Hitachi Code	UPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.050 g

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